Description

JMT Dual N-channel Enhancement Mode Power MOSFET

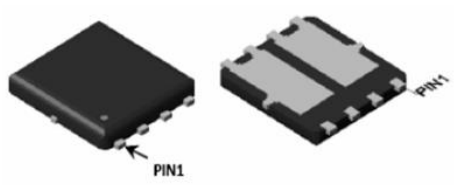
Features

- 60V, 50A
  $R_{DS(ON)}$ <12mΩ @ V_{GS} = 10V
  $R_{DS(ON)}$ <16mΩ @ V_{GS} = 4.5V
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

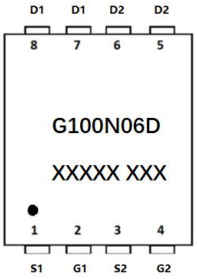
Application

- Load Switch
- PWM Application
- Power management

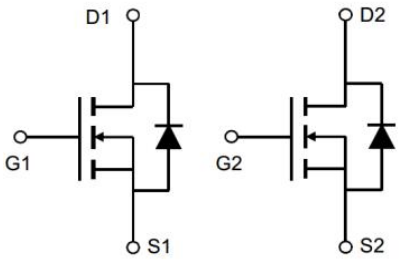
100% UIS TESTED!
100% ΔVds TESTED!



PDFN5X6-8L(Dual)



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
G100N06D	JMTG100N06D	TAPING	PDFN5X6-8L	13inch	2500	25000

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	50	A
		T_C = 100℃	33	A
I_{DM}	Pulsed Drain Current note1		200	A
E_{AS}	Single Pulsed Avalanche Energy note2		100	mJ
P_D	Power Dissipation	T_C = 25℃	51	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.5	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=60V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.7	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=20A	-	9.5	12	mΩ
		V_{GS}=4.5V, I_D=15A	-	11.5	16	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	4605	-	pF
C_{oss}	Output Capacitance		-	215	-	pF
C_{rss}	Reverse Transfer Capacitance		-	191	-	pF
Q_g	Total Gate Charge	V_{DS}=30V, I_D=20A, V_{GS}=10V	-	77	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	23	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=30V, I_D=30A, R_G=1.8Ω, V_{GS}=10V	-	7.1	-	ns
t_r	Turn-on Rise Time		-	5.3	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	27.2	-	ns
t_f	Turn-off Fall Time		-	6.2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=30A, dI/dt=100A/μs	-	29	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	45	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃, V_{DD}=30V, V_G=10V, L=0.5mH, Rg=25Ω, I_{AS}=20A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

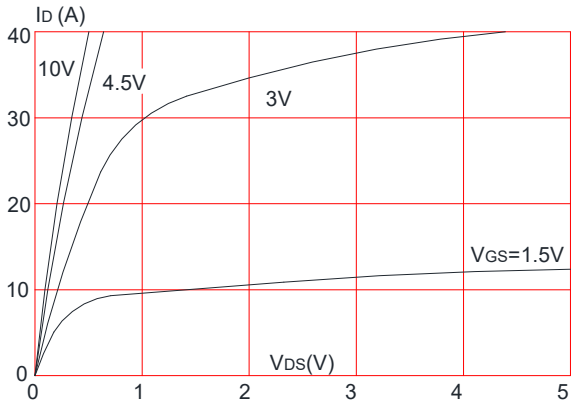


Figure 2: Typical Transfer Characteristics

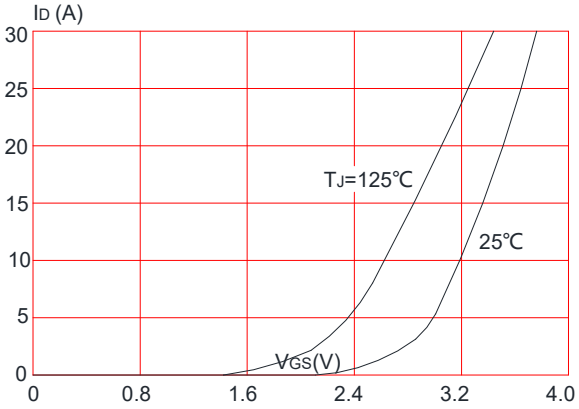


Figure 3: On-resistance vs. Drain Current

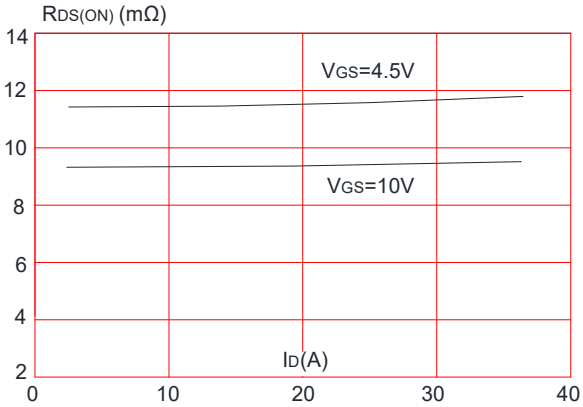


Figure 4: Body Diode Characteristics

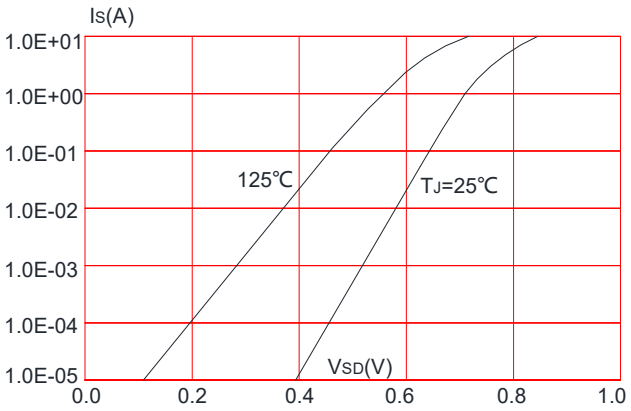


Figure 5: Gate Charge Characteristics

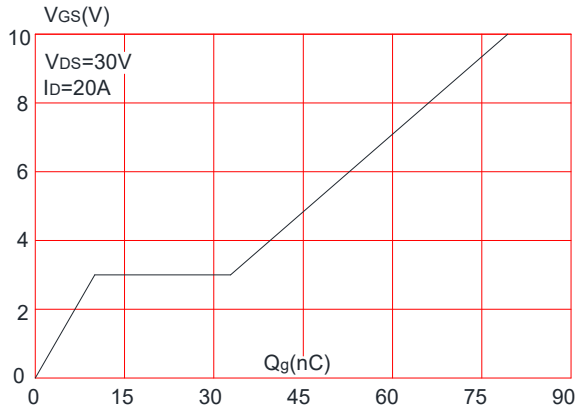


Figure 6: Capacitance Characteristics

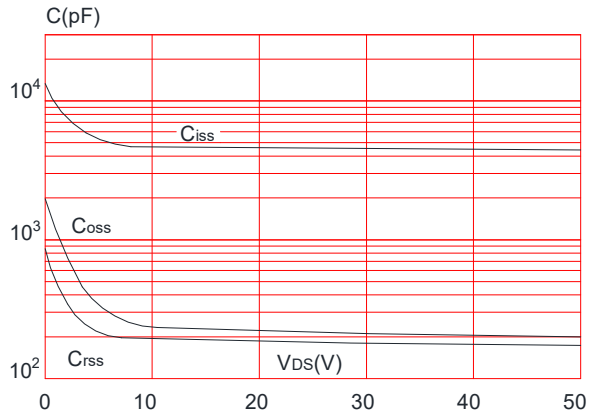


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

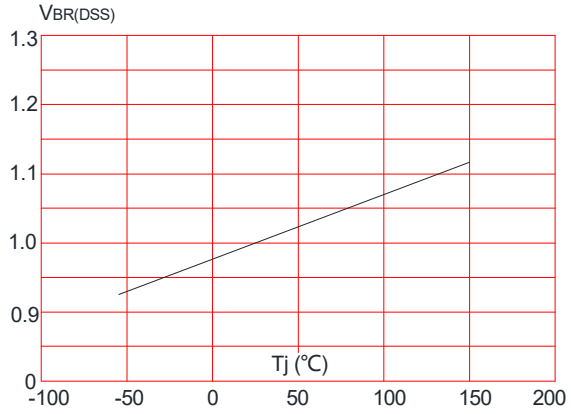


Figure 8: Normalized on Resistance vs. Junction Temperature

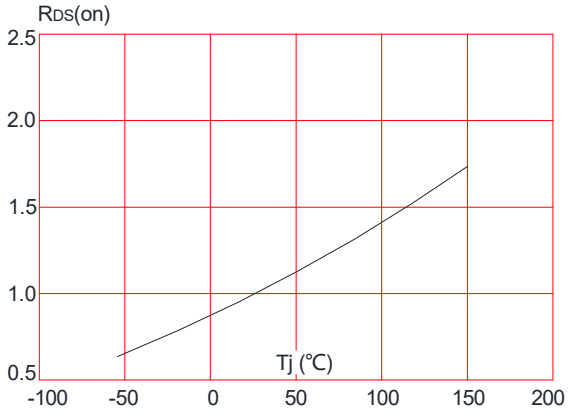


Figure 9: Maximum Safe Operating Area

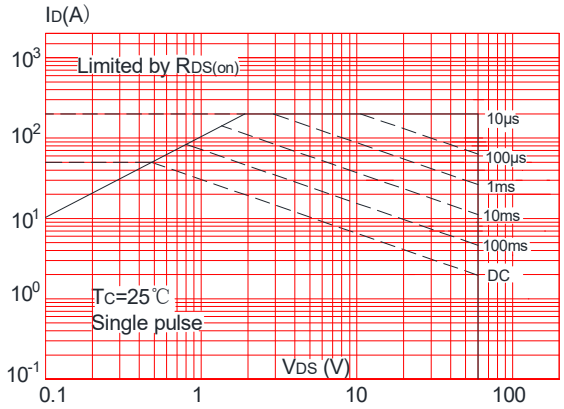


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

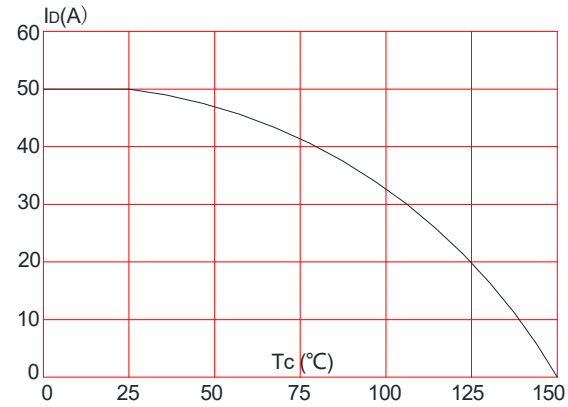
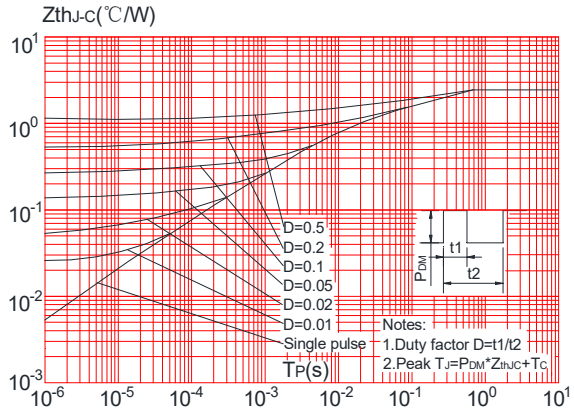


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

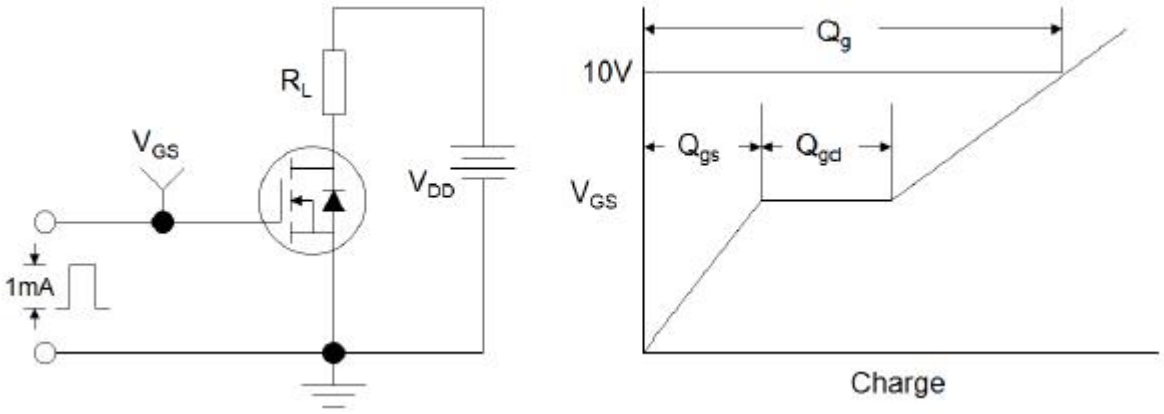


Figure1:Gate Charge Test Circuit & Waveform

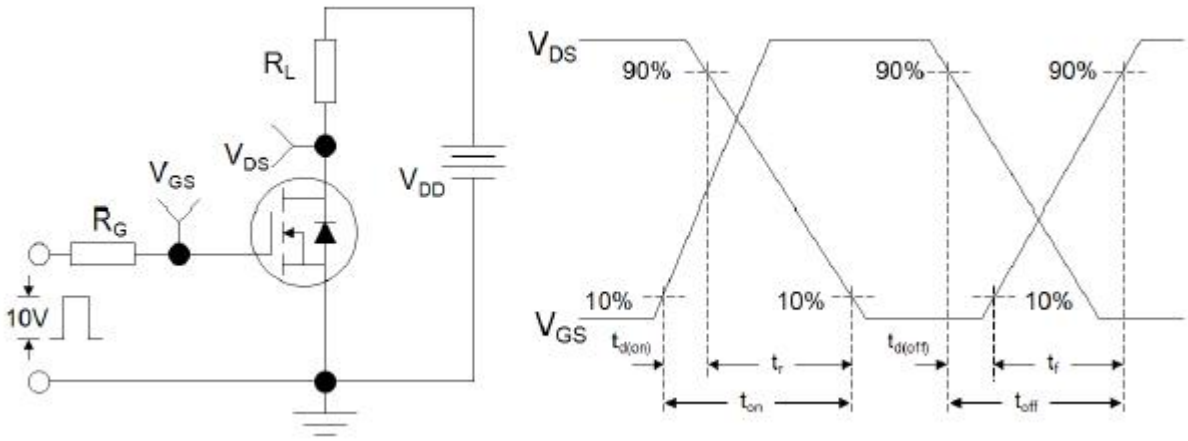


Figure 2: Resistive Switching Test Circuit & Waveforms

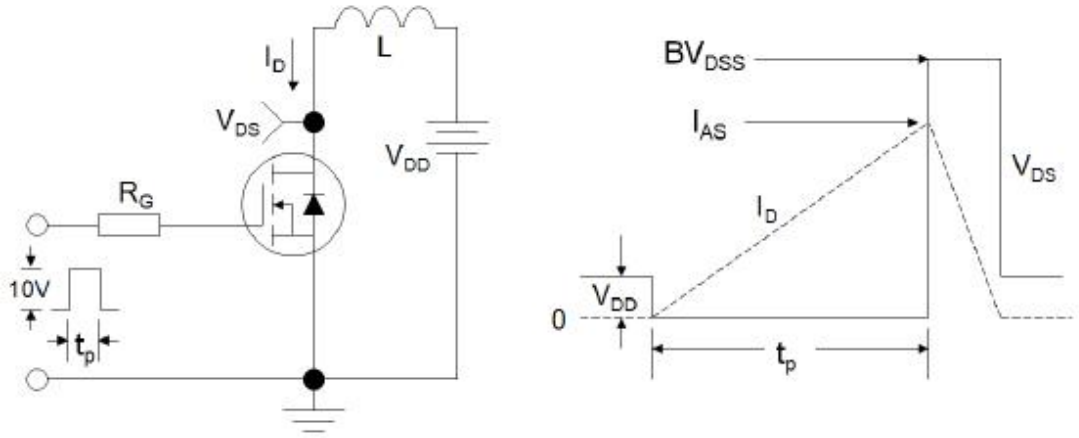
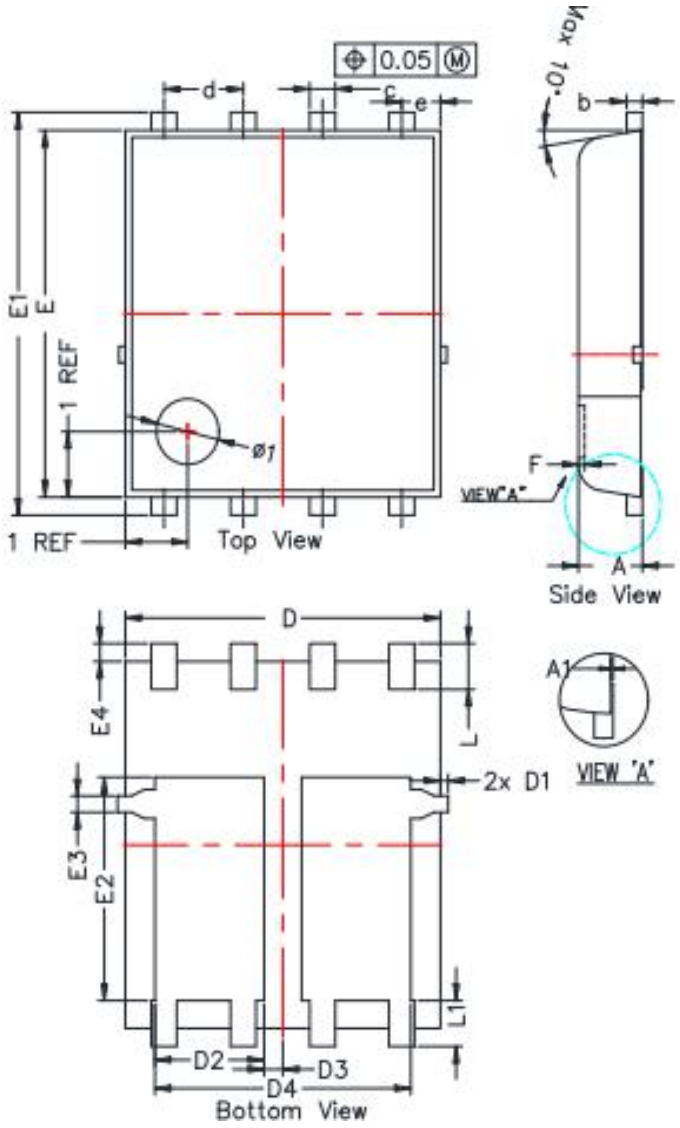


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data- PDFN5X6-8L



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
* A	0.900	1.000	1.100	0.035	0.039	0.043
A1	0.000	---	0.050	0.000	----	0.002
b	0.246	0.254	0.312	0.010	0.010	0.012
* c	0.310	0.410	0.510	0.012	0.016	0.020
d		1.27 BSC			0.050 BSC	
* D	4.950	5.050	5.150	0.195	0.199	0.203
*D1	---	---	0.125	---	---	0.005
*D2	1.650	1.750	1.850	0.065	0.069	0.073
D3	0.200	0.300	0.400	0.008	0.012	0.016
D4	4.000	4.100	4.200	0.157	0.161	0.165
e		0.62 BSC			0.024 BSC	
* E	5.500	5.600	5.700	0.217	0.220	0.224
* E1	6.050	6.150	6.250	0.238	0.242	0.246
E2	3.310	3.410	3.510	0.130	0.134	0.138
E3	0.150	0.250	0.350	0.006	0.010	0.014
* E4	0.175	0.275	0.375	0.007	0.011	0.015
F	-	-	0.100	-	-	0.004
* L	0.500	0.600	0.700	0.02	0.02	0.03
L1	0.600	0.700	0.800	0.02	0.03	0.03